

# ZMM5221B THRU ZMM5267B

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# Formosa MS

# ZMM5221B THRU ZMM5267B

# 500mW Surface Mount Zener Diodes - 2.4V-75V

#### **Features**

- Silicon epitaxial planarchip structure.
- Wide zener reverse voltage range 2.4V to 67V.
- Small package size for high density applications.
- Glass hermetically sealed package.
- Ideally suited for automated assembly processes.
- Lead-free parts meetenvironmental standards of MIL-STD-19500 /228

#### Mechanical data

• Case: GlassMini-Melf / SOD-80

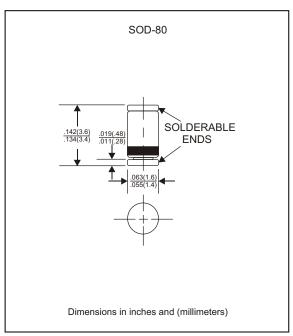
 Terminals:Plated terminals, solderable per MIL-STD-750, Method 2026

• Polarity: Indicated by cathode band

• Mounting Position : Any

• Weight : Approximated 0.03 gram

## Package outline



#### **Maximum ratings** (at T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 200 mADC	V <sub>F</sub>			1.10	V
Power Dissipation		P <sub>D</sub>			500	mW
Storage temperature		T <sub>stg</sub>	-55		+150	°C
Operating temperature		T,	-65		+175	°C

## **Electrical characteristics** (at T<sub>A</sub>=25°C unless otherwise noted)

<b>.</b>	Marking	Zener voltage	Test current		Zener impedance		Lea cur	Surge current	
Part No.	code	V <sub>z</sub> @ I <sub>zT</sub>	I <sub>ZT</sub>	Z <sub>ZT</sub> @ I <sub>ZT</sub>	Z <sub>zK</sub> @ I <sub>zK</sub>	I <sub>zK</sub>	I <sub>R</sub>	V <sub>R</sub>	I <sub>Surge</sub>
		Volts	mA	OHMs	OHMs	mA	uA	Volts	mA
ZMM5221B		2.4	20.0	30	1200	0.25	100	1.0	
ZMM5222B		2.5	20.0	30	1250	0.25	100	1.0	
ZMM5223B		2.7	20.0	30	1300	0.25	75	1.0	
ZMM5224B		2.8	20.0	30	1400	0.25	75	1.0	
ZMM5225B		3.0	20.0	30	1600	0.25	50	1.0	
ZMM5226B		3.3	20.0	28	1600	0.25	25	1.0	
ZMM5227B		3.6	20.0	24	1700	0.25	15	1.0	
ZMM5228B		3.9	20.0	23	1900	0.25	10	1.0	
ZMM5229B		4.3	20.0	22	2000	0.25	5.0	1.0	
ZMM5230B		4.7	20.0	19	1900	0.25	5.0	2.0	
ZMM5231B		5.1	20.0	17	1600	0.25	5.0	2.0	
ZMM5232B		5.6	20.0	11	1600	0.25	5.0	3.0	
ZMM5234B		6.2	20.0	7	1000	0.25	5.0	4.0	
ZMM5235B		6.8	20.0	5	750	0.25	3.0	5.0	
ZMM5236B		7.5	20.0	6	500	0.25	3.0	6.0	
ZMM5237B		8.2	20.0	8	500	0.25	3.0	6.5	
ZMM5238B		8.7	20.0	8	600	0.25	3.0	6.5	
ZMM5239B		9.1	20.0	10	600	0.25	3.0	7.0	
ZMM5240B		10	20.0	17	600	0.25	3.0	8.0	
ZMM5241B		11	20.0	22	600	0.25	2.0	8.4	
ZMM5242B		12	20.0	30	600	0.25	1.0	9.1	
ZMM5243B		13	9.5	13	600	0.25	0.5	9.9	
ZMM5244B		14	9.0	15	600	0.25	0.1	9.0	
ZMM5245B		15	8.5	16	600	0.25	0.1	11	
ZMM5246B		16	7.8	17	600	0.25	0.1	12	
ZMM5247B		17	7.4	19	600	0.25	0.1	13	
ZMM5248B		18	7.0	21	600	0.25	0.1	14	
ZMM5249B		19	6.6	23	600	0.25	0.1	14	
ZMM5250B		20	6.2	25	600	0.25	0.1	15	
ZMM5251B		22	5.6	29	600	0.25	0.1	17	
ZMM5252B		24	5.2	33	600	0.25	0.1	18	
ZMM5253B		25	5.0	35	600	0.25	0.1	19	
ZMM5254B		27	4.6	41	600	0.25	0.1	21	
ZMM5255B		28	4.5	44	600	0.25	0.1	21	
ZMM5256B		30	4.2	49	600	0.25	0.1	23	
ZMM5257B		33	3.8	58	700	0.25	0.1	25	
ZMM5258B		36	3.4	70	700	0.25	0.1	27	
ZMM5259B		39	3.2	80	800	0.25	0.1	30	
ZMM5260B		43	3.0	93	900	0.25	0.1	33	
ZMM5261B		47	2.7	105	1000	0.25	0.1	36	
ZMM5262B		51	2.5	125	1100	0.25	0.1	39	
ZMM5263B		56	2.2	150	1300	0.25	0.1	43	
ZMM5264B		60	2.1	170	1400	0.25	0.1	46	
ZMM5265B		62	2.0	185	1400	0.25	0.1	47	
ZMM5266B		68	1.8	230	1600	0.25	0.1	52	
ZMM5267B		75	1.7	270	1700	0.25	0.1	56	

Note: 5% tolerance of Zenervoltage



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## Rating and characteristic curves (ZMM5221B THRU ZMM5267B)

FIG.1-TOTAL POWER DISSIPATION VS. AMBIENT TEMPERATURE

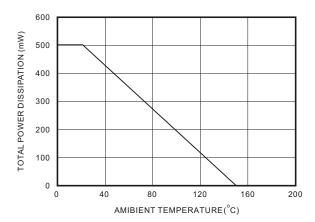


FIG. 2-TYPICAL CHANGE OF WORKING VOLTAGE UNDER OPERATING CONDITIONS AT T<sub>A</sub> =25°C

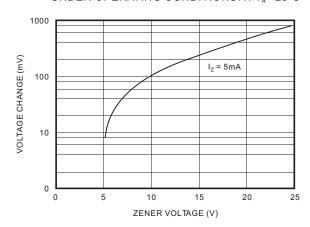


FIG. 3-TYPICAL CHANGE OF WORKING VOLTAGE VS. JUNCTION TEMPERATURE

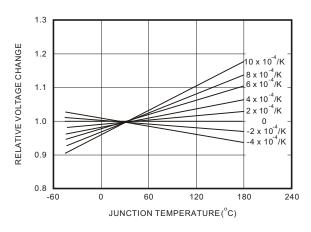


FIG. 4-TEMPERATURE COEFFICIENT OF VZ VS. Z-VOLTAGE

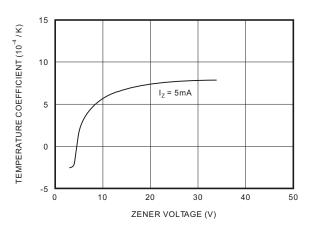
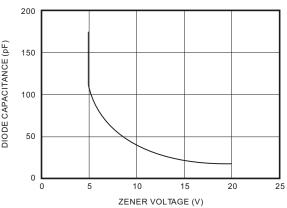


FIG. 5-DIODE CAPACITANCE VS. Z-VOLTAGE



DIODE CAPACITANCE (pF)

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## Rating and characteristic curves (ZMM5221B THRU ZMM5267B)

FIG. 6-FORWARD CURRENT VS. FORWARD VOLTAGE

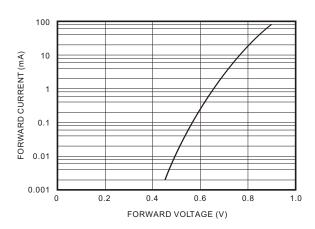


FIG. 7-Z-CURRENT VS. Z-VOLTAGE

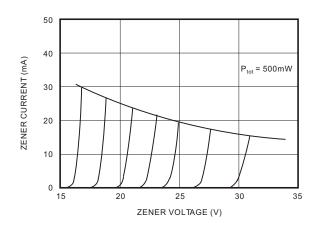


FIG. 8-Z-CURRENT VS. Z-VOLTAGE

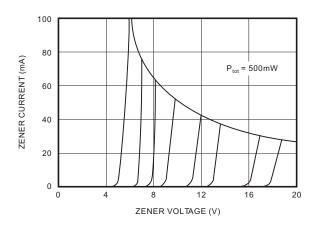


FIG. 9-DIFFERENTIAL Z-RESISTANCE VS. Z-VOLTAGE

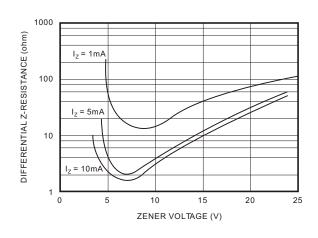
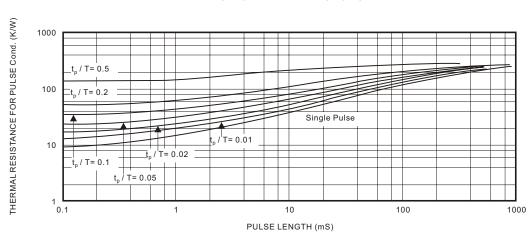


FIG. 10-THERMALRESPONSE





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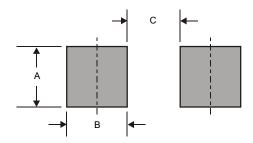


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## **Pinning information**

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode	1 1 2	1 2

## Suggested solder pad layout



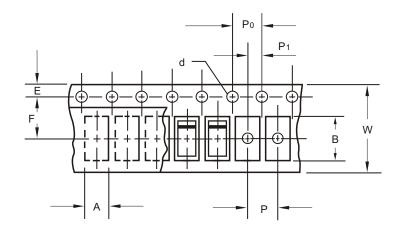
Dimensions in inches and (millimeters)

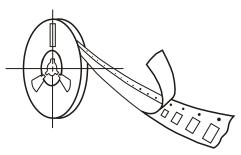
PACKAGE	А	В	С	
SOD-80	0.071 (1.80)	0.035 (0.90)	0.102 (2.60)	

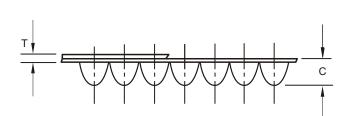
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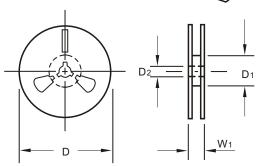
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## **Packing information**









unit:mm

Item	Symbol	Tolerance	SOD-80
Carrier width	Α	0.1	2.00
Carrier length	В	0.1	3.70
Carrier depth	С	0.1	1.80
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D1	min	50.00
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D <sub>2</sub>	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	Р	0.1	4.00
Sprocket hole pitch	P <sub>0</sub>	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	Т	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accor dance with EIA standar RS-481-A and specifications listed above.

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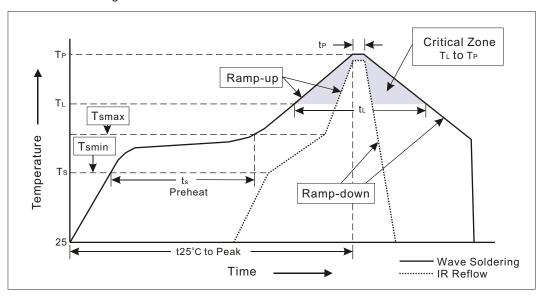
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## Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-80	7"	2500	4.0	25,000	185*120*180	178	400*250*200	100,000	7.0

### Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=10°C~35°C Humidity=65%±15%
- 2.Reflow soldering of surface-mount devices



#### 3. Flow (wave) soldering (solder dipping)

Profile Feature	Soldering Condition
Average ramp-up rate(T∟ to T♭)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min tomax)(ts)	100°C 150°C 60~120sec
Tsmaxto T∟ -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T∟) -Time(t∟)	183°C 60~150sec
Peak Temperature(T <sub>P</sub> )	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(tp)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes



# **ZMM5221B THRU ZMM5267B**

### High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec. immerse body into solder 1/16"±1/32"	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R = V_Z$ at $T_A = 150$ °C for 168 hrs.	MIL-STD-750D METHOD-1026
4. Forward OperationLife	Rated zener current at T=25°C for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}$ C, $I_F = 200$ mA On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	15P <sub>sig</sub> at T <sub>A</sub> =121°C for 4 hrs.	
7. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Thermal Shock	0°C for 5min. rise to 100°C for 5min. total 10 cycles.	MIL-STD-750D METHOD-1056
9. Forward Surge	8.3ms single halfsine-wave superimposed on rated load, one surge.	MIL-STD-750D METHOD-4066-2
10. Humidity	at T <sub>A</sub> =65°C, RH=98% for1000hrs.	MIL-STD-750D METHOD-1038
11. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031
12. Solvent Resistance	Dip into Freonat 25°C for 1 min.	MIL-STD-202F METHOD-215